

Features

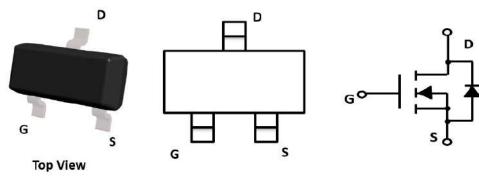
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package
- Available in SOT23 Package

Applications

- PWM applications
- Load switch
- Power management

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VDS	30	V
R DS(on),Typ@ VGS=10 V	25	mΩ
<i>I</i> D	6.5	А

Product Summarv



SOT-23

Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	V
Drain Current – Continuous	I _D	6.5	A
Drain Current- Continuous	I _D (T _a =70℃)	5.2	А
Pulsed Drain Current	I _{DM}	34	A
Gate-Source Voltage	V _{GS}	±20	V
Total Power Dissipation	PD	1.4	W
Total Power Dissipation	P _D (T _a =70℃)	1.0	W
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-55 to 150	°C

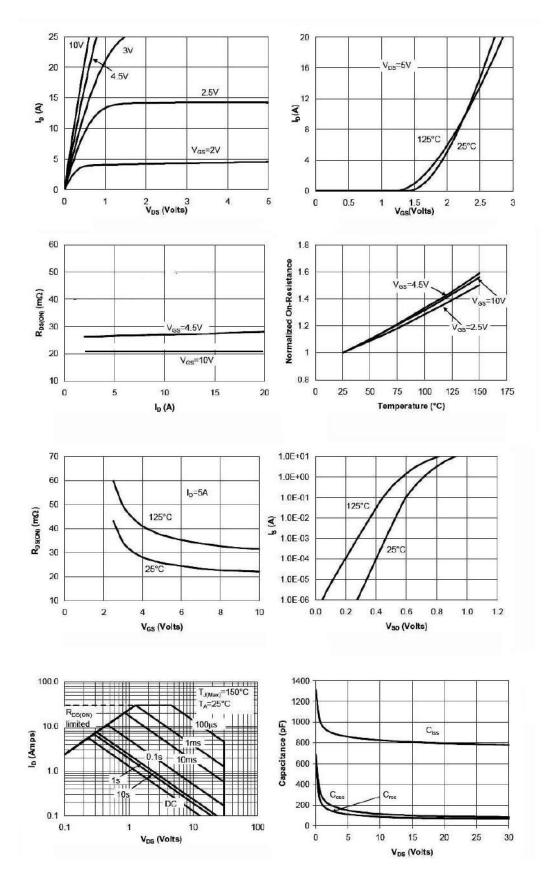


Electrical Characteristics(Ta=25°C)

参数	符号		条件	最小值	典型值	最大值	单位
Parameter	Symbol	Test Co	onditions	Min	Тур	Max	Unit
Drain–Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V	l _D =250µA	30			V
		V _{DS} =24V	V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V T _J =55℃	V _{GS} =0V			5	μA
Gate–Body Leakage.	I _{GSS}	V _{GS} =±20V	$V_{DS}=0V$			±0.1	μA
On–State Drain Current	I _{D(on)}	V _{GS} =4.5V	V_{DS} =5V	30			А
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$	I _D =250μΑ	1.3	1.8	2.3	V
	R _{DS(on)(1)}	V _{GS} =10V	I _D =6.5A		25	35	
Static Drain–Source On–Resistance	R _{DS(on)(2)}	V _{GS} =10V TJ=125℃	I _D =6.5A			55	mΩ
	R _{DS(on)(3)}	V _{GS} =4.5V	I _D =5A		45	50	
Forward Transconductance	g fs	V _{DS} =5V	I _D =5A	8.5			S
Drain–Source Diode Forward Voltage	V_{SD}	V _{GS} =0V	I _S =1A		0.77	1	V
Input Capacitance	C _{iss}				345	690	
Output Capacitance	C _{oss}	V _{DS} =15V f=1MHz			55		pF
Reverse Transfer Capacitance	C _{rss}				32		
Turn–On Delay Time	t _{d(on)}				2.8		
Turn–On Rise Time	t _r	V _{GS} =10V	$R_L=2.7\Omega$		7.2		
Turn–Off Delay Time	t _{d(off)}	V _{DS} =15V	R _{GEN} =6Ω		15.8		ns
Turn–Off Fall Time	t _f				4.6		



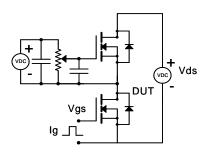
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

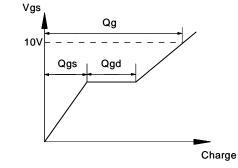




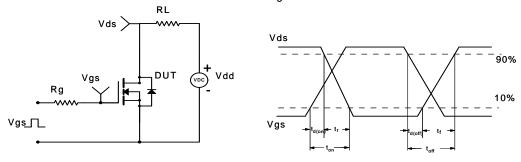
ASDM3404ZA 30V N-Channel MOSFET

Gate Charge Test Circuit & Waveform

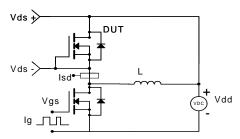


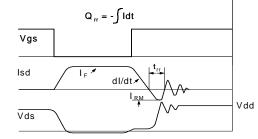


Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms







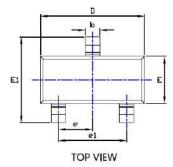
Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM3404ZA-R	3404	SOT-23	Tape&Reel	3000/Reel

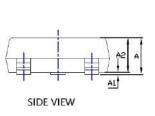
PACKAGE	MARKING
SOT-23	3404

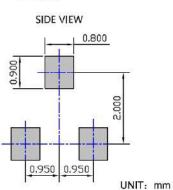


SOT-23 Package information









SUGGESTED SOLDER PAD LAYOUT

	DIMENSIONS						
SYMBOL	INCHES			Millimeter			
	MIN.	NDM.	MAX.	MIN,	NDM.	MAX.	
Α	0.035	10000	0,045	0,900	1000	1.150	
A1	0.000		0.004	0,000		0,100	
A2	0.035	0.038	0.041	0.900	0,975	1.050	
ø	0,012	0.016	0.020	0.300	0.400	0.500	
c	0,004) 	0.008	0.100		0.200	
D	0.110	0.114	0.118	2,800	2,900	3,000	
E	0.047	0,051	0,055	1.200	1.300	1,400	
E1	0,089	0,094	0,100	2,250	2.400	2,550	
е	0.037TYP			0.950TYP			
el	0.071	0,075	0.079	1.800	1.900	2.000	
L	0.022REF			0.022REF 0.550REF			
L1	0.012	0.016	0.200	0,300	0,400	0,500	
୍ଷ	0*		8°	0*		8.	

NOTE:

1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS, 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED. 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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